

<b>PATENT ASSIGNMENT COVER SHEET</b>
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Electronic Version v1.1  
 Stylesheet Version v1.2

EPAS ID: PAT3996680

<b>SUBMISSION TYPE:</b>	NEW ASSIGNMENT
<b>NATURE OF CONVEYANCE:</b>	ASSIGNMENT

**CONVEYING PARTY DATA**

Name	Execution Date
NXP B.V.	08/01/2016

**RECEIVING PARTY DATA**

<b>Name:</b>	NEXPERIA B.V.
<b>Street Address:</b>	HIGH TECH CAMPUS 60
<b>City:</b>	EINDHOVEN
<b>State/Country:</b>	NETHERLANDS
<b>Postal Code:</b>	5656 AG

**PROPERTY NUMBERS Total: 183**

Property Type	Number
Patent Number:	7952333
Patent Number:	8093097
Patent Number:	8062974
Patent Number:	7696783
Patent Number:	7550997
Patent Number:	7659584
Patent Number:	7944658
Patent Number:	8134815
Patent Number:	7839209
Patent Number:	8169084
Patent Number:	7907007
Patent Number:	8184415
Patent Number:	8264801
Patent Number:	8390971
Patent Number:	8258916
Patent Number:	8357971
Patent Number:	8809695
Patent Number:	8901705
Patent Number:	8810004
Patent Number:	8901638

PATENT

<b>Property Type</b>	<b>Number</b>
Patent Number:	8513733
Patent Number:	8324878
Patent Number:	8652904
Patent Number:	8686470
Patent Number:	8441031
Patent Number:	8400193
Patent Number:	8735957
Patent Number:	9129991
Patent Number:	8711532
Patent Number:	9203237
Patent Number:	8493097
Patent Number:	9147732
Patent Number:	9006822
Patent Number:	8508035
Patent Number:	9130553
Patent Number:	9048116
Patent Number:	8847235
Patent Number:	8981566
Patent Number:	9263335
Patent Number:	9064847
Patent Number:	9349819
Patent Number:	9268351
Patent Number:	9368963
Patent Number:	9190826
Patent Number:	9091741
Patent Number:	9331028
Patent Number:	9236734
Patent Number:	8962461
Patent Number:	9190237
Patent Number:	9171837
Patent Number:	9116533
Patent Number:	9331155
Patent Number:	9397569
Patent Number:	9230953
Patent Number:	9305789
Patent Number:	9386642
Patent Number:	9425130
Patent Number:	9385115

<b>Property Type</b>	<b>Number</b>
<b>Patent Number:</b>	6100712
<b>Patent Number:</b>	6342428
<b>Patent Number:</b>	6674129
<b>Patent Number:</b>	5753561
<b>Patent Number:</b>	6013558
<b>Patent Number:</b>	6057227
<b>Patent Number:</b>	5977800
<b>Patent Number:</b>	6140188
<b>Patent Number:</b>	6010939
<b>Patent Number:</b>	6221759
<b>Patent Number:</b>	6465311
<b>Patent Number:</b>	6154018
<b>Patent Number:</b>	6314154
<b>Patent Number:</b>	6150234
<b>Patent Number:</b>	6084462
<b>Patent Number:</b>	6060871
<b>Patent Number:</b>	6251730
<b>Patent Number:</b>	6255692
<b>Patent Number:</b>	6144085
<b>Patent Number:</b>	6175225
<b>Patent Number:</b>	6495421
<b>Patent Number:</b>	6125027
<b>Patent Number:</b>	6417564
<b>Patent Number:</b>	6583485
<b>Patent Number:</b>	7528459
<b>Patent Number:</b>	7579900
<b>Patent Number:</b>	7330046
<b>Patent Number:</b>	5717347
<b>Patent Number:</b>	6566708
<b>Patent Number:</b>	6664593
<b>Patent Number:</b>	6603291
<b>Patent Number:</b>	6707100
<b>Patent Number:</b>	6855601
<b>Patent Number:</b>	6825105
<b>Patent Number:</b>	6800900
<b>Patent Number:</b>	6717787
<b>Patent Number:</b>	6780714
<b>Patent Number:</b>	6534367

<b>Property Type</b>	<b>Number</b>
Patent Number:	6784488
Patent Number:	7439582
Patent Number:	7253459
Patent Number:	7102337
Patent Number:	7122860
Patent Number:	7504690
Patent Number:	8344448
Patent Number:	7629647
Patent Number:	7671440
Patent Number:	7408223
Patent Number:	7696599
Patent Number:	7579649
Patent Number:	7361555
Patent Number:	8222693
Patent Number:	7394144
Patent Number:	7737507
Patent Number:	7843259
Patent Number:	7504307
Patent Number:	8742825
Patent Number:	7772100
Patent Number:	5712197
Patent Number:	5930653
Patent Number:	5910670
Patent Number:	5966616
Patent Number:	6218222
Patent Number:	6541817
Patent Number:	6359308
Patent Number:	6368921
Patent Number:	6420755
Patent Number:	6498071
Patent Number:	6436779
Patent Number:	6600194
Patent Number:	6319777
Patent Number:	6559502
Patent Number:	6521498
Patent Number:	6936890
Patent Number:	6833583
Patent Number:	6861875

<b>Property Type</b>	<b>Number</b>
<b>Patent Number:</b>	7312526
<b>Patent Number:</b>	7265574
<b>Patent Number:</b>	7459750
<b>Patent Number:</b>	7262460
<b>Patent Number:</b>	7199010
<b>Patent Number:</b>	7485534
<b>Patent Number:</b>	7726011
<b>Patent Number:</b>	7482669
<b>Patent Number:</b>	7728404
<b>Patent Number:</b>	7304526
<b>Patent Number:</b>	8159032
<b>Patent Number:</b>	6544860
<b>Patent Number:</b>	6326283
<b>Patent Number:</b>	6433622
<b>Patent Number:</b>	6222353
<b>Patent Number:</b>	6380721
<b>Patent Number:</b>	6551881
<b>Patent Number:</b>	7485916
<b>Application Number:</b>	13264816
<b>Application Number:</b>	13502229
<b>Application Number:</b>	13288570
<b>Application Number:</b>	14703731
<b>Application Number:</b>	14644272
<b>Application Number:</b>	14180418
<b>Application Number:</b>	14056648
<b>Application Number:</b>	14499654
<b>Application Number:</b>	14059831
<b>Application Number:</b>	14704692
<b>Application Number:</b>	14693756
<b>Application Number:</b>	14835403
<b>Application Number:</b>	14322553
<b>Application Number:</b>	14668154
<b>Application Number:</b>	14802840
<b>Application Number:</b>	14874189
<b>Application Number:</b>	14478866
<b>Application Number:</b>	14984880
<b>Application Number:</b>	15044005
<b>Application Number:</b>	14984614

Property Type	Number
Application Number:	14743038
Application Number:	14801635
Application Number:	15049419
Application Number:	14530189
Application Number:	14849469
Application Number:	14988443
Application Number:	14746612
Application Number:	14879394
Application Number:	14725366
Application Number:	15187162
Application Number:	15060548

**CORRESPONDENCE DATA**

**Fax Number:** (408)518-5671

*Correspondence will be sent to the e-mail address first; if that is unsuccessful, it will be sent using a fax number, if provided; if that is unsuccessful, it will be sent via US Mail.*

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**Correspondent Name:** NXP SEMICONDUCTORS

**Address Line 1:** 411 EAST PLUMERIA DRIVE, MS41

**Address Line 4:** SAN JOSE, CALIFORNIA 95134

**NAME OF SUBMITTER:** VILIMAINA NAGA

**SIGNATURE:** /Vilimaina Naga/

**DATE SIGNED:** 08/08/2016

**Total Attachments: 10**

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## DEED OF TRANSFER OF THE LEGAL TITLE TO CERTAIN PATENTS

THIS AGREEMENT IS DATED 1 AUGUST 2016 AND MADE BETWEEN:

THE UNDERSIGNED:

(1) NXP B.V., residing at High Tech Campus 60, 5656 AG Eindhoven, the Netherlands, a Dutch entity, with seat in Eindhoven, the Netherlands, Trade Register number 17070622 (the "**Seller**");

and

(2) Nexperia B.V., residing at High Tech Campus 60, 5656 AG Eindhoven, the Netherlands, a Dutch entity, with seat in Nijmegen, the Netherlands, Trade Register number 66264111 (the "**Company**");

together also to be referred to as "**Parties**" and each party individually as a "**Party**", as the case may be,

**BACKGROUND:**

(A) The Parties have entered into an intellectual property sale and purchase agreement dated 1 August 2016 relating to the sale and purchase of (among others) certain patents (the "**IPSPA**").

(B) Pursuant to the IPSPA the Seller has sold the legal title to the patents identified in Schedule 1 (the "**Transferred Patents**") to the Company and has agreed to transfer the legal title to the Transferred Patents to the Company in this deed (the "**Deed**").

(C) The Parties hereby wish to transfer the legal title to the Transferred Patents to the Company on the terms and conditions as set out in this Deed.

**THE PARTIES AGREE AS FOLLOWS:**

### 1 DEFINITIONS

Any capitalized term used in this Deed but not defined will have the same meaning as ascribed to it in the IPSPA or the IPTLA.

### 2 TRANSFER OF LEGAL OWNERSHIP OF THE TRANSFERRED IP

By this Deed, the Seller assigns, transfers, conveys and delivers to the Company its legal title to the Transferred Patents, including the right to sue and claim

damages or any other remedies for any act of infringement prior to the Effective Date, and for the avoidance of doubt, the right to claim priority relating to any of the Transferred Patents, and the Company hereby accepts from Seller such assignment, transfer, conveyance and delivery. Seller authorizes and requests the relevant national or international Patent Office, or any other Office for Intellectual Property worldwide to record the Company as the owner of the Transferred Patents in the relevant patent register.

**3 VARIATION TO THE DEED**

No variation, extension, cancellation or translation of any expressed terms of this Deed (including in Schedule 1) will be binding upon Seller or the Company unless made in writing and signed by duly authorized representatives of Seller and the Company.

**4 ADDITIONAL ASSIGNMENT DOCUMENTS; FURTHER ASSURANCE**

The Seller will be responsible for effectuating the registration of the assignment and transfer of the Transferred Patents. Seller and the Company shall, at each other's request, execute and do all such deeds, documents, acts and things as the requesting Party may from time to time reasonably require in order to effectuate or formalize the transfer of the Transferred Patents to the Company and to cause the Transferred Patents to be recorded at the relevant patent registers around the world in the name of the Company.

**5 OBSERVANCE OF LEGAL REQUIREMENTS**

The Company and Seller undertake to observe and act in accordance with all applicable legal conditions and terms required in order to effectuate the registration of the assignment and transfer of the Transferred Patents in the relevant registers.

**6 COSTS FOR REGISTRATION**

Without prejudice to Clause 8.4 of the IPTLA, the costs for the registration of the assignment and transfer of the Transferred IP in the relevant registers will be borne by the Seller.

**7 APPLICABLE LAW AND JURISDICTION**

This Deed will be governed by and construed in accordance with the laws of the Netherlands. Any action or proceeding in respect of any claim arising out of or related to this Deed will be conducted by Seller and the Company in accordance with the dispute settlement procedure provided in the IPSPA.



**8 NO RESCISSION AND NO NULLIFICATION**

Each Party hereby waives its right to rescind (*ontbinden*) this Deed on the basis of Section 6:265 of the Dutch Civil Code.

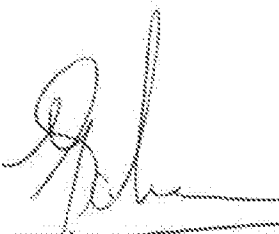
**IN EVIDENCE WHEREOF**, the Parties have caused this Deed to be signed by their duly authorized representatives effective as of 1 August 2016.



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**NXP B.V.**

By: *G.E.C. Dierckx*  
Title: *Authorized signatory*



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**Nexperia B.V.**

By: *J.A.W. Schreurs*  
Title: *Director*

Execution version

**Schedule 1** Transferred Patents

Schedule 1 Transferred Patents 01August2016

NXP Reference Number	Status	Title	Region	PriorityDate	FiledDate	ApplicationNumber	PublicationNumber	PatentNumber	Owners
000922US1	Granted	Method to improve accuracy, linearity and temperature drift of Current Sense MOSFET's	US	2005-06-01	2006-05-30	11/916110	US20080191779	US7952333	NXP B.V.
000909US1	Granted	Layer Sequence and Method of Manufacturing a Layer Sequence	US	2005-06-15	2006-06-12	11/917092	US20080206588	US7903097	NXP B.V.
001018CN1	Granted	Semiconductor Device with Grounding Structure	CN	2005-08-09	2006-07-31	200680029211.1	US2008029211.1	CN200680029211	NXP B.V.
001018US1	Granted	Semiconductor Device with Grounding Structure	US	2005-08-09	2006-07-31	11/997240	US20080237785	US8062974	NXP B.V.
001563US1	Granted	Area efficient multiplexer based logic blocks for FRGAs	US	2005-09-05	2006-09-04	12/065634	US20080234732	US7665783	NXP B.V.
002087US3	Granted	4-Level Logic Decoder	US	2005-07-22	2006-07-21	11/956315	US20080211543	US7550997	NXP B.V.
003984CN04	Granted	A substrate isolated integrated High Voltage Diode with Shallow Trench Isolation inside the Unit Cell	CN	2005-12-19	2006-12-12	200680047677.4	CN10131612	CN200680047677	NXP B.V.
003984US2	Granted	A substrate isolated integrated High Voltage Diode with Shallow Trench Isolation inside the Unit Cell	US	2005-12-19	2006-12-12	12/158108	US20080255227	US7669584	NXP B.V.
006172CN	Granted	ESD protection for external decoupling grounds	CN	2006-06-20	2007-06-15	200780023275.5	CN101473437	CN200780023275	NXP B.V.
006172JP	Granted	ESD protection for external decoupling grounds	JP	2006-06-20	2007-06-15	2009-516033	US20090185317	JP5069745	NXP B.V.
006172US1	Granted	ESD protection for external decoupling grounds	US	2006-06-20	2007-06-15	12/705686	US20090185317	US7944658	NXP B.V.
006172US2	Granted	INTEGRATED CIRCUIT AND ASSEMBLY THEREWITH	US	2007-06-15	2007-06-15	13/030695	CN1015141639	US8134915	NXP B.V.
006642CN	Granted	Buried Gate Tunnel MOSFET	CN	2006-10-08	2007-10-03	200780036958.4	CN101523607	CN200780036958	NXP B.V.
006642US1	Granted	Buried Gate Tunnel MOSFET	US	2006-10-08	2007-10-03	12/444140	US20100197135	US7839709	NXP B.V.
007085US1	Granted	Soft solder metal on top of passivation layer below top surface level	US	2006-11-13	2007-11-12	12/514289	US20100192348	US8169084	NXP B.V.
007085US2	Granted	Soft solder metal on top of passivation layer below top surface level	CN	2006-11-13	2007-11-12	200780042015.2	CN101536184	CN200780042015	NXP B.V.
007085DE03	Granted	Soft solder metal on top of passivation layer below top surface level	DE	2006-11-13	2007-11-12	07849095.0	EP2002561	DE602007039739	NXP B.V.
007288US	Granted	A commutating auto zero amplifier with low output noise and improved accuracy	US	2006-10-27	2007-10-19	12/447278	US20100045378	US7907007	NXP B.V.
007868US1	Granted	3D system level ESD protection in passive substrate	US	2007-02-12	2008-02-08	12/525129	US20100085672	FR2134415	NXP B.V.
007868DE03	Granted	3D system level ESD protection in passive substrate	FR	2007-02-12	2008-02-08	082709970.1		FR2134415	NXP B.V.
007868DE04	Granted	3D system level ESD protection in passive substrate	DE	2007-02-12	2008-02-08	082709970.1		DE602008016170	NXP B.V.
007868CN03	Granted	Arrangement and Approach for Coupling Power Supplies Using Controlled Switching Techniques	CN	2007-02-12	2008-02-08	082709970.1		GB2130226	NXP B.V.
01049923US03	Granted	Arrangement and Approach for Coupling Power Supplies Using Controlled Switching Techniques	US	2007-11-30	2008-11-27	20080118109.8	CN101897100	CN20080118109	NXP B.V.
01049949US03	Granted	Current Flow Optimised Single Finger ESD Protection Structure	US	2007-11-30	2008-11-27	12/745275	US20100301673	US7264801	NXP B.V.
01052505EP2	Published	Meander resistor improvements for ESD purposes	EP	2008-09-11	2009-09-09	09787147.9	EP2335283	US7335283	NXP B.V.
01052505US04	Granted	Meander resistor improvements for ESD purposes	US	2008-09-11	2009-09-09	13/063189	US20100216459	US8390971	NXP B.V.
01051180US04	Granted	Enhanced RESUR Stepped Oxide Concept	US	2007-10-29	2008-10-22	09723012.1	EP2308088	US8289816	NXP B.V.
01051180US05	Granted	Enhanced RESUR Stepped Oxide Concept	FR	2007-10-29	2008-10-22	12/739341	US20100320532	US3357321	NXP B.V.
01051180DE06	Granted	Enhanced RESUR Stepped Oxide Concept	DE	2007-10-29	2008-10-22	08843598.7	US8343987	FR2026154	NXP B.V.
01051180US07	Granted	Enhanced RESUR Stepped Oxide Concept	GB	2007-10-29	2008-10-22	08843598.7	US20100807988	GB2206154	NXP B.V.
01057065EP03	Published	Trench Gate Semiconductor Device and Method of Manufacturing Thereof	EP	2008-05-28	2009-05-20	09734266.6	EP2286455	US8206154	NXP B.V.
01342039CN03	Granted	Design- and processing method for building mesh-structured semiconductor devices with improved metal adhesion avoiding increased undercutting and metal grooves	CN	2007-11-27	2008-10-22	200880117821.6	CN101874301	CN200880117821	NXP B.V.
01342039US05	Granted	Design- and processing method for building mesh-structured semiconductor devices with improved metal adhesion avoiding increased undercutting and metal grooves	US	2007-11-27	2008-10-22	12/744368	US20100244275	US8809695	NXP B.V.
0134434US04	Granted	ESD protection devices with integrated capacitors with high capacitance density, high operating voltage and high accuracy resistors	US	2008-10-28	2009-10-22	13/126233	US20110204480	US8901705	NXP B.V.
01346707US03	Granted	METHODS, SYSTEMS AND DEVICES FOR ELECTROSTATIC DISCHARGE PROTECTION	US	2009-11-26	2009-11-26	13/502807	US20120205780	US8810004	NXP B.V.
01330999EP03	Published	Low Voltage Non-Resurf Trenchmos	EP	2008-07-25	2009-07-27	09786726.1	EP2308095	US8308095	NXP B.V.
01330999US04	Granted	Low Voltage Non-Resurf Trenchmos	US	2008-07-25	2009-07-27	13/055742	US20110121384	US9016138	NXP B.V.
01339596US04	Published	Lead passivation in PLZT cover layer for providing a smooth low-dielectric cover layer for the deposition of reliable high-quality resistors	US	2009-04-20	2010-04-14	13/764816	US20120045881		NXP B.V.
01338326CN02	Granted	A 3D RESUR EGD TERMINATION	CN	2010-08-16	2011-08-12	201110230833.3	CN102376750	CN20110230833	NXP B.V.
01338326US03	Granted	EDGE TERMINATION REGION	US	2010-08-16	2011-08-15	13/210308	US20120073980	US8513733	NXP B.V.
01338326DE04	Granted	A 3D RESUR EGD TERMINATION	DE	2010-08-16	2010-08-16	10172933.3	DE60201008171	DE60201008171	NXP B.V.
01337908US03	Granted	VOLTAGE REGULATOR WITH GATE RESISTOR FOR IMPROVED EFFICIENCY	US	2009-10-22	2010-10-22	12/610959	US20110101952	US8334878	NXP B.V.
01330103CN03	Granted	Surge protection device manufactured in a double side process	CN	2009-10-22	2010-10-22	201008047531.6	CN1010576740	CN201008047531	NXP B.V.
01339435US02	Granted	Surge protection device manufactured in a double side process	US	2010-09-21	2011-09-20	13/237878	US20120200976	US8652904	NXP B.V.
01339435DE03	Granted	Improved Reliability of Gate Buffer under Clip	DE	2010-09-21	2010-09-21	10178090.6	US20120070983	DE602010020096	NXP B.V.
01339435FR04	Granted	Improved Reliability of Gate Buffer under Clip	FR	2010-09-21	2010-09-21	10178090.6	US201201515672	FR2432023	NXP B.V.
01339435GB05	Granted	Improved Reliability of Gate Buffer under Clip	GB	2010-09-21	2011-01-07	12/786970	US8686470	GB2432023	NXP B.V.
01339778US01	Granted	ESD PROTECTION CIRCUIT	US	2011-01-07	2012-01-05	12/150305.6	US201201515672	US8686470	NXP B.V.
01339778DE03	Granted	ESD PROTECTION CIRCUIT	DE	2011-01-07	2012-01-05	12/150305.6	US201201515672	FR2475008	NXP B.V.
01339778FR04	Granted	ESD PROTECTION CIRCUIT	FR	2011-01-07	2012-01-05	12/150305.6	US201201515672	FR2475008	NXP B.V.
01339778GB05	Granted	ESD PROTECTION CIRCUIT	GB	2011-01-07	2011-01-05	13/016443	US201201515672	GB2475008	NXP B.V.
01406887US01	Granted	ESD Protection Device	US	2011-01-28	2012-01-18	13/016443	US201201515672	US8444031	NXP B.V.
01406887CN02	Granted	ESD Protection Device	CN	2011-01-28	2012-01-18	13/016443	CN102623449	CN201201515672	NXP B.V.
01406887EP03	Published	ESD Protection Device	EP	2011-01-28	2012-01-24	121525254.4	EP2482314		NXP B.V.

Schedule 1 Transferred Patents 01August2016

81406887DE04	Allowed	ESD Protection Device	DE	2011-01-28	2012-01-24	12152254.4	US201310114169	CN103094893	NXP B.V.
81409292US01	Published	CN05 ADJUSTABLE OVER VOLTAGE ESD AND SURGE PROTECTION FOR LED APPLICATION	US	2011-11-03	2012-10-29	137288570	US201310114169	CN103094893	NXP B.V.
81409292CN02	Granted	CN05 ADJUSTABLE OVER VOLTAGE ESD AND SURGE PROTECTION FOR LED APPLICATION	CN	2011-11-03	2012-10-29	2012-10-29	US201310114169	CN103094893	NXP B.V.
81409292DE04	Granted	CN05 Adjustable Over-Voltage, ESD and Surge Protection for LED Application	DE	2011-11-03	2012-08-13	12180332.4	DE602012001969	FR8590218	NXP B.V.
81409292GB06	Granted	CN05 Adjustable Over-Voltage, ESD and Surge Protection for LED Application	GB	2011-11-03	2012-08-13	12180332.4	GB2590218	GB2590218	NXP B.V.
81409938US01	Published	BACKDRIVE PROTECTION CIRCUIT	US	2011-03-21	2012-03-14	137052271	US2012042372	US201400193	NXP B.V.
81413430CN02	Granted	Half Bridge Input Capacitance Integrated into a Power MOSFET	CN	2011-08-02	2012-08-01	12159584.2	EP2930690	CN102916010	NXP B.V.
81413430US03	Granted	Half Bridge Input Capacitance Integrated into a Power MOSFET	US	2011-08-02	2012-07-16	131549684	US20130181772	US8735957	NXP B.V.
81413430US04	Granted	Half Bridge Input Capacitance Integrated into a Power MOSFET	US	2011-08-02	2012-07-16	147249204	US20140207049	US9129991	NXP B.V.
81415814EP01	Published	Method for parasitic modulation of the sheet resistance of AlGaN/GaN heterostructures for a better on-resistance /breakdown voltage trade-off.	EP	2011-12-19	2011-12-19	11184254.6	EP2608268		NXP B.V.; TSMC
81415814CN02	Published	Method for parasitic modulation of the sheet resistance of AlGaN/GaN heterostructures for a better on-resistance /breakdown voltage trade-off.	CN	2011-12-19	2012-12-17	2012-12-17	CN103165668		NXP B.V.; TSMC
81415814US04	Published	Semiconductor Device	US	2012-11-14	2015-05-04	147703731	US20150236095	US20150236095	NXP B.V.; TSMC
81416301CN02	Granted	Integrated Advance Copper Fuse Combined with ESD/Over-Voltage/Reverse Polarity Protection	CN	2011-08-24	2012-08-23	137216328	US20130060883	US8711532	NXP B.V.
81416301EP03	Published	Integrated Advance Copper Fuse Combined with ESD/Over-Voltage/Reverse Polarity Protection	EP	2011-08-24	2012-08-02	2012-08-02	CN102956635	CN201210302940	NXP B.V.
81416751US01	Published	PROTECTION CIRCUIT	US	2012-04-24	2012-04-24	131454862	US20130279053	US92203237	NXP B.V.
81416751CN02	Published	PROTECTION CIRCUIT	CN	2012-04-24	2013-04-22	2013-04-22	CN103490399		NXP B.V.
81418015US01	Granted	CURRENT SENSING CIRCUIT	US	2011-08-16	2013-08-16	137211055	US20130043941	US8443097	NXP B.V.
81418015CN02	Published	GROUP 13 NITRIDE SEMICONDUCTOR DEVICE AND METHOD OF ITS MANUFACTURE	CN	2012-05-09	2012-08-13	2012-08-13	CN102955058	CN102955058	NXP B.V.
81421708US03	Granted	GROUP 13 NITRIDE SEMICONDUCTOR DEVICE AND METHOD OF ITS MANUFACTURE	US	2012-05-09	2013-05-08	2013-05-08	US20130390639	CN103390639	NXP B.V.
81421708DE04	Granted	GROUP 13 NITRIDE SEMICONDUCTOR DEVICE AND METHOD OF ITS MANUFACTURE	DE	2012-05-09	2012-05-09	137687065	DE602012006262	US9147732	NXP B.V.
81421708FR05	Granted	GROUP 13 NITRIDE SEMICONDUCTOR DEVICE AND METHOD OF ITS MANUFACTURE	FR	2012-05-09	2012-05-09	12167365.1	FR6628884	FR6628884	NXP B.V.
81422840US04	Granted	ADVANCED RESUME CONCEPT FOR LV TRENCHMOS (HFG - ID380)	US	2011-12-07	2012-10-14	131659262	US20130146967	US9006822	NXP B.V.
81422840US04	Published	ADVANCED RESUME CONCEPT FOR LV TRENCHMOS (HFG - ID380)	US	2011-12-07	2015-03-11	147444272	US20150187913	US8508035	NXP B.V.
81423241US01	Granted	Circuit connector apparatus and method therefor	US	2011-12-02	2012-11-28	137309878	US20130140705	US8508035	NXP B.V.
81423241CN02	Granted	Circuit connector apparatus and method therefor	CN	2011-12-02	2012-11-28	2012-11-28	CN201210495227	CN201210495227	NXP B.V.
81426343US01	Granted	LOW/HIGH VOLTAGE SELECTOR	US	2012-10-04	2012-10-04	137645339	US20140097866	US9130553	NXP B.V.
81427050CN02	Published	Spoke Suppression in half bridge circuits through increased CBD achieved via isolation trench connection	CN	2011-12-07	2012-12-05	2012-12-05	CN103151532		NXP B.V.
81427050US04	Granted	SEMICONDUCTOR DEVICE HAVING ISOLATION TRENCHES	US	2011-12-07	2012-11-21	137682792	US20130146972	US9004816	NXP B.V.
81427617DE03	Granted	CASCODED SEMICONDUCTOR DEVICES	DE	2012-07-30	2012-07-30	1316937451	US8842735	US8842735	NXP B.V.
81428281CN02	Published	ELECTRONIC DEVICE AND METHOD OF MANUFACTURING SUCH DEVICE	CN	2012-06-19	2012-06-17	12178518.2	DE602012010268	DE602012010268	NXP B.V.
81428281EP01	Published	DISCRETE SEMICONDUCTOR DEVICE PACKAGE AND MANUFACTURING METHOD	EP	2012-06-19	2012-06-17	12170528.9	EP2669936	EP2669936	NXP B.V.
81428281US02	Granted	DISCRETE SEMICONDUCTOR DEVICE PACKAGE AND MANUFACTURING METHOD	US	2012-06-01	2013-05-08	137690055	US20130320551	US9281566	NXP B.V.
814284852CN03	Published	DISCRETE SEMICONDUCTOR DEVICE PACKAGE AND MANUFACTURING METHOD	CN	2012-06-01	2013-05-29	2013-05-29	CN102456705	US9190826	NXP B.V.
814284851US03	Granted	DISCRETE SEMICONDUCTOR DEVICE PACKAGE AND MANUFACTURING METHOD	US	2012-06-01	2013-05-08	147607587	US20150140739	US9263335	NXP B.V.
814294938US03	Published	TRANSISTOR WITH REDUCED PARASITIC	US	2014-02-14	2014-02-14	147480418	US20150256090	GB2726170	NXP B.V.
814294938CN02	Published	TRANSISTOR WITH REDUCED PARASITIC	CN	2014-02-14	2015-02-05	2015-02-05	CN104851914	GB2726170	NXP B.V.
814294938EP01	Published	HETEROJUNCTION SEMICONDUCTOR DEVICE AND MANUFACTURING METHOD	EP	2012-05-22	2012-05-22	12168384.0	EP267415	EP267415	NXP B.V.
814294938CN02	Published	HETEROJUNCTION SEMICONDUCTOR DEVICE AND MANUFACTURING METHOD	CN	2012-05-22	2013-05-17	2013-05-17	CN103428194	US9064847	NXP B.V.
814295073US03	Granted	HETEROJUNCTION SEMICONDUCTOR DEVICE AND MANUFACTURING METHOD	US	2012-05-22	2013-05-18	147895228	US20130320400	US9064847	NXP B.V.
814295073CN04	Application	HETEROJUNCTION SEMICONDUCTOR DEVICE AND MANUFACTURING METHOD	CN	2012-05-22	2015-05-18	147714927			NXP B.V.
81526196EP01	Published	Method for Leakage Matching in High Voltage Gain devices in Cascade arrangement	EP	2013-03-28	2013-03-28	13161707.8	EP2784816		NXP B.V.
81526196CN02	Published	Method for Leakage Matching in High Voltage Gain devices in Cascade arrangement	CN	2013-03-28	2014-02-17	2014-02-17	CN104078461		NXP B.V.
81526196US03	Granted	Method for Leakage Matching in High Voltage Gain devices in Cascade arrangement	US	2013-03-28	2014-03-28	147208188	US20140292287	US9268351	NXP B.V.
81526950EP01	Published	CASCODED SEMICONDUCTOR DEVICES	EP	2012-11-23	2013-11-23	12194083.7	EP2726171		NXP B.V.
81526950US03	Published	CASCODED SEMICONDUCTOR DEVICES	US	2012-11-23	2013-10-17	2013-10-17	CN103840821		NXP B.V.
81527056EP01	Published	ESD PROTECTION	EP	2012-11-23	2012-12-06	147056648	US20140145208		NXP B.V.
81527056CN02	Published	ESD PROTECTION	CN	2012-12-06	2013-12-04	2013-12-04	EP2741330		NXP B.V.
81527056US03	Allowed	ESD PROTECTION	US	2012-12-06	2013-11-05	147072122	US20140166077		NXP B.V.
81527347CN02	Published	CASCODED SEMICONDUCTOR DEVICES	CN	2012-11-23	2013-11-19	2013-11-19	CN103855703		NXP B.V.
81527347US03	Granted	CASCODED SEMICONDUCTOR DEVICES	US	2012-11-23	2013-11-19	147084441	US20140146428		NXP B.V.
81527347DE04	Granted	CASCODED SEMICONDUCTOR DEVICES	DE	2012-11-23	2012-11-23	12194065.4	DE602012008012		NXP B.V.
81527347GB05	Granted	CASCODED SEMICONDUCTOR DEVICES	GB	2012-11-23	2012-11-23	12194065.4			NXP B.V.
81527756US01	Granted	A PROPORTIONAL INTEGRAL DERIVATIVE (PID) ANALOG CONTROLLER AND A METHOD FOR TESTING A PID	US	2012-12-05	2012-12-05	137706508	US20140152339	US9091741	NXP B.V.
81527756EP02	Published	A PROPORTIONAL INTEGRAL DERIVATIVE (PID) ANALOG CONTROLLER AND A METHOD FOR TESTING A PID	EP	2012-12-05	2013-10-02	13187114.7	EP2841408		NXP B.V.
81530905EP01	Published	A Field Emission ESD Protection Device with Field Enhanced Electrode Structure	EP	2013-06-26	2013-06-26	13173864.3	EP2819165		NXP B.V.
81530905CN02	Published	A Field Emission ESD Protection Device with Field Enhanced Electrode Structure	CN	2013-06-26	2014-06-25	2014-06-25	CN104253022		NXP B.V.

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81.53.09.051US03	Allowed	A Field Emission ESD Protection Device with Field Enhanced Electrode Structure	US	2013-06-26	2014-06-02	14/293146	US201510001671		NXP B.V.
81.53.14.94.FE01	Published	A lateral field emission ESD protection device with well defined cathode-anode distance	EP	2013-06-26	2013-06-26	131/73868.4	EP2819166		NXP B.V.
81.53.14.94.CN02	Published	A lateral field emission ESD protection device with well defined cathode-anode distance	CN	2013-06-26	2014-06-11	14/201445	CN104253021		NXP B.V.
81.53.18.09.US03	Granted	ELECTRIC FIELD GATE DEVICE AND MANUFACTURING METHOD	US	2013-06-26	2014-06-11	14/201445	US20150002966	US92246734	NXP B.V.
81.53.18.09.US02	Published	GN HEAT/ AND GAN DIODES	CN	2012-12-19	2013-12-16	14/108042	CN103887334		NXP B.V.
81.53.18.09.US03	Granted	GN HEAT/ AND GAN DIODES	US	2012-12-19	2013-12-16	14/108042	US20140167064	US9262461	NXP B.V.
81.53.19.91.US01	Granted	Electrode Coating for Electron Emission Devices with Cavities	US	2012-12-19	2013-12-16	14/261246	US20150311103	US9192037	NXP B.V.
81.53.19.91.US02	Published	Electrode Coating for Electron Emission Devices with Cavities	CN	2014-04-24	2014-04-24	14/5109715.9	CN105006414		NXP B.V.
81.53.19.91.EP03	Published	Electrode Coating for Electron Emission Devices with Cavities	EP	2014-04-24	2015-03-26	15161025.0	EP2937887		NXP B.V.
81.53.33.60.CN02	Published	CASCODE CIRCUIT FOR Electron Emission Devices with Cavities	CN	2012-12-17	2013-12-13	201310684492.6	CN103872006		NXP B.V.
81.53.33.60.US03	Granted	CASCODE CIRCUIT	US	2012-12-17	2013-12-03	14/094890	US20140167382	US9171837	NXP B.V.
81.53.66.38.FE01	Published	Integrated gate circuit to enable reverse conduction of GAN cascode switch configurations	EP	2013-04-05	2013-04-05	13162597.2	EP2787641		NXP B.V.
81.53.66.38.US03	Granted	Integrated gate circuit to enable reverse conduction of GAN cascode switch configurations	CN	2013-04-05	2014-04-04	201410154635.9	CN104104384		NXP B.V.
81.53.66.38.US02	Published	Integrated gate circuit to enable reverse conduction of GAN cascode switch configurations	US	2013-04-05	2014-03-17	14/215242	US20140300410		NXP B.V.
81.53.66.38.EP01	Published	The use of TiW/N in NXP's GAN Schottky process Platform	EP	2013-04-15	2013-04-15	13163745.6	EP2793285	US9116533	NXP B.V.
81.53.66.38.CN02	Published	The use of TiW/N in NXP's GAN Schottky process Platform	CN	2013-04-15	2014-04-14	201410147957.6	CN104103684		NXP B.V.
81.53.66.38.US03	Allowed	The use of TiW/N in NXP's GAN Schottky process Platform	US	2013-04-15	2014-04-09	14/249108	US20140306312		NXP B.V.
81.54.61.42.FE01	Published	SiGe diode with Reduced Surface Field Effect structure	EP	2013-10-02	2013-10-02	13187183.2	EP2881117		NXP B.V.
81.54.61.42.CN02	Published	SiGe diode with Reduced Surface Field Effect structure	CN	2013-10-02	2014-09-29	201410514957.8	CN104518035		NXP B.V.
81.54.61.42.US03	Published	SiGe diode with Reduced Surface Field Effect structure	US	2013-10-02	2014-09-29	14/699654	US20150091023		NXP B.V.
81.58.88.04.US01	Published	ANTENNA RESONANCE FREQUENCY CONTROL DRIVER	US	2013-10-22	2013-10-22	14/059831	US20150188448		NXP B.V.
81.58.88.04.CN02	Published	ANTENNA RESONANCE FREQUENCY CONTROL DRIVER	CN	2013-10-22	2014-10-21	201410563005.5	CN105177358		NXP B.V.
81.58.901.EP02	Published	SEMICONDUCTOR DEVICE AND MANUFACTURING METHOD	EP	2014-05-08	2014-07-10	14176389.4	EP2942315		NXP B.V.
81.58.901.US03	Application	Diffusion barrier capping layers on Ni Schottky gate based devices	CN	2014-05-08	2015-05-06	2015102269888.0			NXP B.V.
81.58.901.US04	Published	Diffusion barrier capping layers on Ni Schottky gate based devices	US	2014-05-08	2015-05-05	14/704692	US20150325698		NXP B.V.
81.59.10.88.FE01	Published	Proposal to use parallel power mosfets in softstart / hotswap and other current controlled applications such that the safe operating area of each device is protected	EP	2013-08-30	2013-08-30	13182494.8	EP2843496		NXP B.V.
81.59.10.88.CN02	Published	Proposal to use parallel power mosfets in softstart / hotswap and other current controlled applications such that the safe operating area of each device is protected	CN	2013-08-30	2014-08-22	201410418576.X	CN104426515		NXP B.V.
81.59.10.88.US03	Published	Proposal to use parallel power mosfets in softstart / hotswap and other current controlled applications such that the safe operating area of each device is protected	US	2013-08-30	2014-08-11	14/450062	US20150061620		NXP B.V.
81.59.2616.CN03	Application	Trench Schottky Diode with Wide Trench Termination	US	2014-05-14	2015-05-13	2015102140970.3			NXP B.V.
81.59.2616.US04	Published	Trench Schottky Diode with Wide Trench Termination	US	2014-05-14	2015-04-22	14/693756	US20150333133		NXP B.V.
81.61.71.21.FE01	Published	Unidirectional ESD protection device based on a vertical SCR	EP	2013-10-21	2013-10-21	131895933.0	EP2863432		NXP B.V.
81.61.71.21.CN02	Published	Unidirectional ESD protection device based on a vertical SCR	CN	2013-10-21	2014-10-17	201410503798.2	CN104516638		NXP B.V.
81.61.71.21.US03	Granted	Unidirectional ESD protection device based on a vertical SCR	US	2013-10-21	2014-10-17	14/516978	US20150108346	US92230933	NXP B.V.
81.62.50.66.FE02	Published	Schottky barrier tuning with nitrogen in TiW/N gates on GAN	EP	2014-05-08	2014-07-09	14176384.9	EP2942305		NXP B.V.
81.62.50.66.CN03	Published	Schottky barrier tuning with nitrogen in TiW/N gates on GAN	CN	2014-05-08	2015-04-15	2015101278296.0	CN105607990		NXP B.V.
81.62.50.66.US04	Granted	Schottky barrier tuning with nitrogen in TiW/N gates on GAN	US	2014-05-08	2015-04-22	14/693118	US20150325667	US9305789	NXP B.V.
81.62.53.33.FE01	Published	Electronic slope control circuit for cascoded power semiconductor devices	EP	2014-09-25	2014-09-25	14186451.2	EP3001563		NXP B.V.
81.62.53.33.CN02	Application	Electronic slope control circuit for cascoded power semiconductor devices	CN	2014-09-25	2015-09-23	201510613256.4			NXP B.V.
81.62.53.33.US03	Published	Electronic slope control circuit for cascoded power semiconductor devices	US	2014-09-25	2015-08-25	14/835403	US20150094218		NXP B.V.
81.62.53.47.FE01	Application	Integrated clamp circuit for insulated gate cascoded power semiconductor devices	EP	2014-07-02	2015-07-01	15182739.1			NXP B.V.
81.62.69.73.CN02	Published	Exposed Die Quad Flat No-Leads (DFN) Package	CN	2014-07-02	2015-07-01	201510378353.X	CN105244294		NXP B.V.
81.62.69.81.US01	Application	Exposed-Heatsink Quad Flat No-Leads (DFN) Package	US	2014-07-02	2015-07-01	14/322553			NXP B.V.
81.62.69.81.CN02	Published	Exposed-Heatsink Quad Flat No-Leads (DFN) Package	CN	2014-07-02	2015-07-01	201510378835.5	CN105304506		NXP B.V.
81.62.77.57.FE02	Published	Capacitance reduction of ESD protection devices	EP	2014-05-19	2014-05-19	14176516.2	EP2947691		NXP B.V.
81.62.77.57.CN03	Published	Capacitance reduction of ESD protection devices	CN	2014-05-19	2015-05-18	201510251633.4	CN105609787		NXP B.V.
81.62.77.57.US04	Published	Capacitance reduction of ESD protection devices	US	2014-05-19	2015-05-05	14/708788	US20150333119		NXP B.V.
81.62.78.55.FE01	Published	The use of sacrificial PECVD nitride for better manufacturability of NXP's GAN Schottky process of record	EP	2014-04-11	2014-04-11	14164449.2	EP2930754		NXP B.V.
81.62.78.55.US02	Published	The use of sacrificial PECVD nitride for better manufacturability of NXP's GAN Schottky process of record	US	2014-04-11	2015-03-25	14/668154	US20150295051		NXP B.V.
81.62.87.62.FE01	Published	Symmetric HV EMDOS with split gate field plate	EP	2014-08-05	2014-08-05	14179923.9	CN10533210		NXP B.V.
81.62.87.62.CN02	Published	Symmetric HV EMDOS with split gate field plate	CN	2014-08-05	2015-07-31	201510462961.9	CN10536788		NXP B.V.
81.62.87.62.US03	Published	Symmetric HV EMDOS with split gate field plate	US	2014-08-05	2015-07-17	14/602840	US20160043708		NXP B.V.
81.62.93.04.CN02	Application	LEADLESS SEMICONDUCTOR DEVICE AND METHOD OF MAKING THEREOF	CN	2014-10-29	2015-10-27	201510703546.8			NXP B.V.
81.62.93.04.FE01	Application	Packaging solution to obtain low current collapse for GAN Schottky Barrier Diodes	EP	2014-12-03	2014-12-03	14196049.2			NXP B.V.
81.62.93.04.CN02	Application	Packaging solution to obtain low current collapse for GAN Schottky Barrier Diodes	CN	2014-12-03	2015-12-02	201510868768.5			NXP B.V.
81.62.93.04.US03	Application	Packaging solution to obtain low current collapse for GAN Schottky Barrier Diodes	US	2014-12-03	2015-10-02	14/874189	US20150311103		NXP B.V.
81.62.93.04.FE01	Application	Hybrid SiGe / Si Schottky Diode	EP	2015-01-30	2015-01-30	15153336.1			NXP B.V.
81.62.93.04.US02	Application	Hybrid SiGe / Si Schottky Diode	US	2015-01-30	2015-01-30	14/6984880			NXP B.V.
81.62.93.04.CN01	Application	Shockley Diode used in an ESD/ECOS protection device	EP	2015-03-09	2015-03-09	15158272.3			NXP B.V.
81.62.93.04.US02	Application	Shockley Diode used in an ESD/ECOS protection device	US	2015-03-09	2015-02-15	15/044005			NXP B.V.
81.62.93.04.FE01	Application	a fully symmetric common mode choke	EP	2015-01-20	2015-01-20	15151828.9			NXP B.V.
81.62.93.04.CN02	Application	a fully symmetric common mode choke	CN	2015-01-20	2016-01-19	201610034290.0			NXP B.V.
81.62.93.04.US03	Application	a fully symmetric common mode choke	US	2015-01-20	2015-12-30	14/6984614			NXP B.V.

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81640640FP01	Published	Connecting wire for side solderable multiple leads terminal (support market demand for DSN packages of side solderable on multiple leads end)	EP	2014-08-01	2014-08-01	14179517.9	EP2980945	NXP B.V.
81640640CN02	Published	Connecting wire for side solderable multiple leads terminal (support market demand for DSN packages of side solderable on multiple leads end)	CN	2014-08-01	2015-07-29	201510454935.1	CN105321919	NXP B.V.
81641834US01	Published	Connecting wire for side solderable multiple leads terminal (support market demand for DSN packages of side solderable on multiple leads end)	US	2014-08-01	2015-07-16	147801635	US20160035651	NXP B.V.
81641834CN02	Application	PACKAGE WITH MULTIPLE I/O SIDE-SOLDERABLE TERMINALS	CN	2014-10-29	2015-10-29	147827365		NXP B.V.
81644279CN02	Application	PACKAGE WITH MULTIPLE I/O SIDE-SOLDERABLE TERMINALS	CN	2014-10-29	2015-10-29	201510711207.4		NXP B.V.
81644279CN02	Application	Expose Die & Chip Scale Package embedded with encapsulated mold compound	EP	2015-03-06	2015-03-06	15157936.4		NXP B.V.
81644279US03	Application	Expose Die & Chip Scale Package embedded with encapsulated mold compound	CN	2015-03-06	2016-03-04	201610124596.5		NXP B.V.
81645442US01	Application	Expose Die & Chip Scale Package embedded with encapsulated mold compound	US	2015-03-06	2016-02-22	157609419		NXP B.V.
81645442US01	Application	Autonomous Power Supply	US	2014-10-31	2014-10-31	146750389		NXP B.V.
81645442EP03	Application	Autonomous Power Supply	CN	2014-10-31	2015-10-30	20151027366.3		NXP B.V.
81645442EP03	Application	Autonomous Power Supply	EP	2014-10-31	2015-09-22	151586263.8	EP3016242	NXP B.V.
81647296EP01	Published	Autonomous Power Supply	JP	2014-10-31	2015-09-09	151586263.8		NXP B.V.
81647296CN02	Application	Via on via metallization to reduce capacitance	EP	2014-10-08	2014-10-08	14188213.4	EP3007224	NXP B.V.
81647296CN02	Application	Via on via metallization to reduce capacitance	CN	2014-10-08	2015-10-08	201510645378.1		NXP B.V.
81647296US03	Published	Via on via metallization to reduce capacitance	US	2014-10-08	2015-09-09	147849469		NXP B.V.
81647304EP01	Application	Integrated SCR and Diode as bidirectional ESD protection	EP	2014-10-08	2014-10-08	14188198.7	EP3007232	NXP B.V.
81647304CN02	Application	Integrated SCR and Diode as bidirectional ESD protection	CN	2014-10-08	2015-09-29	201510632924.8		NXP B.V.
81649812EP01	Application	chip scale semiconductor device	US	2014-10-08	2015-09-08	146784803		NXP B.V.
81649812CN02	Application	chip scale semiconductor device	EP	2015-01-27	2015-01-27	15152673.8		NXP B.V.
81649812US03	Application	chip scale semiconductor device	CN	2015-01-27	2016-01-26	201610052223.1		NXP B.V.
81649812US03	Application	chip scale semiconductor device	US	2015-01-27	2016-01-05	1467888443		NXP B.V.
81649832EP01	Application	Built up lead frame / substrate DFN Package with side solderable terminals	US	2015-06-22	2015-06-22	147474612		NXP B.V.
81649832CN02	Application	Built up lead frame / substrate DFN Package with side solderable terminals	EP	2014-12-10	2014-12-10	14197250.5		NXP B.V.
81649832US03	Application	Poly Field Plate Design for Trench MOS Components	CN	2014-12-10	2015-12-10	201510916758.4		NXP B.V.
81649832US03	Application	Poly Field Plate Design for Trench MOS Components	US	2014-12-10	2015-10-09	1467879394		NXP B.V.
81652148EP01	Application	INTERFACE APPARATUS WITH LEAKAGE MITIGATION	US	2015-05-29	2015-05-29	146725366		NXP B.V.
81652603EP01	Application	Spatial distribution of different types of passivation layers on ILL N semiconductor	EP	2015-12-10	2015-12-10	15159187.4		NXP B.V.
81652622EP01	Application	Proper metal contact to p-GaN layer to reduce dynamic on-resistance	EP	2015-11-27	2015-11-27	151596730.4		NXP B.V.
81663020EP01	Application	Leadframe Package with Cleaved Metal Inset Structure on Leadframe	EP	2015-12-20	2015-12-20	15200716.6		NXP B.V.
81672034EP01	Application	Water back grooving before metal application	EP	2015-09-29	2015-09-29	15195639.8		NXP B.V.
81672034CN01	Application	Chip-scale package transistor with front-side contact solder pads	EP	2015-09-11	2015-09-11	15187379.1		NXP B.V.
81672034EP01	Application	DEEP (B) Graded Profile Engineering HV for 3 and 4 terminal TrenchMOS	EP	2015-09-11	2015-09-11	15184799.3		NXP B.V.
81676497EP01	Application	Full water-moulded dual half cut chip-scale package process	EP	2015-07-27	2015-07-27	15178458.4		NXP B.V.
81678210CN01	Application	Laser ablation method to make solderable side lead of leadless packages with 3 or more I/O leads at a axis	CN	2015-12-01	2015-12-01	15150867964.0		NXP B.V.
81678210CN01	Application	Dual Site Solderable Pads (SSP-2) Package concept	CN	2015-08-21	2015-08-21	201510518287.1		NXP B.V.
816789354EP01	Application	Packaging solution to obtain shielding against electromagnetic interference for GaN HEMTs used as high-side switches	EP	2015-11-11	2015-11-11	151594122.6		NXP B.V.
81679734CN01	Application	Frameless Package	CN	2015-12-11	2015-12-11	201510919622.9		NXP B.V.
81684082EP01	Application	Controlling of GaN Cascode Floating-Node Voltage	EP	2016-01-18	2016-01-18	15151746.1		NXP B.V.
81689549EP01	Application	Use of a "grated body contact" to ensure optimal device triggering in GGNMOS ESD protections.	EP	2015-10-27	2015-10-27	151591760.6		NXP B.V.
81689575EP01	Application	DSN0603LY side protection - Water level Package Concept (Laser Via)	EP	2015-11-11	2015-11-11	151594136.6		NXP B.V.
81689575EP01	Application	SHALLOW ISOLATION FOR WAFER LEVEL - CHIP-SCALE PACKAGE DEVICES	EP	2015-12-15	2015-12-15	15200095.6		NXP B.V.
81689575EP01	Application	Insulated gate GaN HEMTs with local Schottky contacts to improve device robustness	EP	2016-01-05	2016-01-05	15150164.8		NXP B.V.
81692019EP01	Application	Integrated resistor on a GaN Die	EP	2016-01-18	2016-01-18	15151749.5		NXP B.V.
81694981US01	Application	Plasma etched overmolded chip scale package	US	2016-03-03	2016-03-03	157606548		NXP B.V.
A001317US	Granted	OUTPUT DRIVER CIRCUIT WITH JUMP START FOR CURRENT SINK	US	1997-12-17	09/992290	09/992290		NXP B.V.
A023763US	Granted	METHOD FOR A CONSISTENT SHALLOW TRENCH ETCH PROFILE	US	1999-10-04	09/411758	09/411758		NXP B.V.
A0238808R	Granted	BI-DIRECTIONAL ESD STRUCTURE	KR	1999-12-17	2001.7010388	2001.7010388	KR20010102184	NXP B.V.
A0238808W	Granted	BI-DIRECTIONAL ESD STRUCTURE	TW	1999-12-17	089126209	089126209	TW478134	NXP B.V.
A0238818R	Granted	IMPROVED ESD DIODE STRUCTURE	KR	1999-12-17	2000.12.08	2001.7010364	KR20010102167	NXP B.V.
A0238818W	Granted	IMPROVED ESD DIODE STRUCTURE	TW	1999-12-17	2000-12-08	089126223		NXP B.V.
A0238818W	Granted	IMPROVED ESD DIODE STRUCTURE	TW	1999-12-17	1999-12-17	097466411	TW477055	NXP B.V.
A0506800S	Granted	SHALLOW TRENCH ISOLATION STRUCTURE AND METHOD FOR MAKING SAME	US	1996-09-30	08/729039	08/729039		NXP B.V.
A050755US	Granted	SHALLOW TRENCH ISOLATION STRUCTURE AND METHOD FOR MAKING SAME	US	1997-08-06	08/920709	08/920709		NXP B.V.
A050821US	Granted	OXIDE ETCH STOP TECHNIQUES FOR UNIFORM DAMASCENE TRENCH DEPT	US	1997-06-23	08/880580	08/880580		NXP B.V.
A050821US	Granted	DIFFERENTIAL MOS CURRENT MODE LOGIC CIRCUIT HAVING HIGH GAIN AND FAST SPEED	US	1997-10-20	08/955012	08/955012		NXP B.V.
A050973US	Granted	SEMICONDUCTOR DEVICE HAVING LOAD DEVICE WITH TRENCH ISOLATION	US	1998-03-31	09/083251	09/083251		NXP B.V.
A050976US	Granted	SHALLOW TRENCH CAPACITIVE STRUCTURES FOR SUPPRESSING INDUCTIVE	US	1998-03-31	09/052865	09/052865		NXP B.V.
A0509901USA	Granted	METHOD FOR FORMING ALIGNED VIA UNDER TRENCHES IN A DUAL DAM	US	1998-06-19	09/100639	09/100639		NXP B.V.
A0509901USA	Granted	MOSFET STRUCTURE HAVING IMPROVED SOURCE/DRAIN JUNCTION PERFORMANCE	US	1998-09-01	09/326936	09/326936		NXP B.V.
A051190US	Granted	HIGH DIFFERENTIAL IMPEDANCE LOAD	US	1999-09-01	09/388034	09/388034		NXP B.V.
A051231US	Granted	NON-POWER-OF-TWO GRAY CODE COUNTER AND BINARY INCREMENTER TH	US	1999-11-04	09/434218	09/434218		NXP B.V.
A051241US	Granted	TRENCH DIFFUSION CORNER ROUNDING IN SHALLOW TRENCH (ST) PRO	US	1999-12-16	09/465151	09/465151		NXP B.V.
B034178US	Granted	POWER/S/C TEMPERATURE SENSE (DIODE/MOST) CIRCUIT	US	1997-08-08	09/129809	09/129809		NXP B.V.

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B 034205US	Granted	VOLTAGE REGULATOR +REF. FOR S/C POWER DEVICES	US	1997-10-17	1998-10-16	09/174222	US6060871	NXP B.V.
B 034265US	Granted	TRENCH MOST WITH POLYSILICON SIDEWALL SOURCE	US	1998-07-11	1999-07-11	09/348960	US6251730	NXP B.V.
B 034272US	Granted	MOSFET/IGBT WITH SILICON-GERMANIUM SOURCE	US	1998-08-14	1999-08-12	09/372961	US6255692	NXP B.V.
B 034274US	Granted	DIFFERENTIAL TEMPERATURE SENSE CELLS IN POWER MOS	US	1998-08-20	1999-08-19	09/372375	US6144085	NXP B.V.
B 034280US	Granted	DC-DC CONVERTER WITH SELF-ADJUSTING POWER FEED	US	1999-07-02	2000-06-29	08/606340	US6175275	NXP B.V.
B 034290US	Granted	COOL D MOSFETS USING SELECTIVE EPITAXIAL GROWTH	US	1999-12-15	2000-12-14	09/738921	US6495421	NXP B.V.
D 096109US	Granted	COMPONENT WITH A CAPACITOR	US	1996-07-31	2000-12-14	08/703143	US6175027	NXP B.V.
D 096116US	Granted	SEMICONDUCTORS WITH METAL LAYER	US	2000-01-27	2001-01-25	09/769179	US2010017421	NXP B.V.
D 030189US1	Granted	SCHEMATIC DIAGRAM	US	2000-03-20	2004-05-25	09/819281	US2010042862	NXP B.V.
D 030275US1	Granted	MONOLITHIC INTEGRATED PUNCH THROUGH DIODE	US	2003-05-27	2004-05-25	10/561885	US5148459	NXP B.V.
D 030303US1	Granted	OPERATION AND CIRCUITRY OF A POWER CONVERSION AND CONTROL.	US	2003-08-12	2004-08-20	10/567396	US5729900	NXP B.V.
F 095150US	Granted	FAILURE PREDICTION FOR PARALLEL MOSFETS	US	2003-09-03	2004-08-20	10/570211	US20070007519	NXP B.V.
G 000215US	Granted	LOW VOLTAGE LOGIC CELL	US	1995-04-12	1996-04-12	08/631385	US5173747	NXP B.V.
G 000249US	Granted	TRENCH MOSFET STRUCTURE WITH LOW CGD AND GATE PROTECTION	US	2000-11-17	2001-11-16	09/093201	US5662708	NXP B.V.
G 000256US	Granted	TRENCH MOSFET WITH LOW QGD/CGD	US	2001-03-23	2002-03-15	09/099698	US6664593	NXP B.V.
G 000257US	Published	AUTONOMOUS SYNCHRONOUS RECTIFIER	GB	2001-03-28		02/714878.3	GB1388208	NXP B.V.
G 000280US	Granted	MOSFET DRIVER WITH DUAL FLOATING GATES, LOCAL SOURCE CONNECT	EP	2001-02-06		02/715637.1	EP1360763	NXP B.V.
G 000280US	Granted	MOSFET DRIVER WITH DUAL FLOATING GATES, LOCAL SOURCE CONNECT	KR	2001-02-06		2002-7013347	KR20020093025	NXP B.V.
G 000280US	Granted	MOSFET DRIVER WITH DUAL FLOATING GATES, LOCAL SOURCE CONNECT	US	2001-02-06	2002-02-04	10/066991	US20020175661	NXP B.V.
G 000280US	Granted	MOSFET DRIVER WITH DUAL FLOATING GATES, LOCAL SOURCE CONNECT	JP	2001-02-06		2002-563598	JP4067967	NXP B.V.
G 000280US	Allowed	MOSFET DRIVER WITH DUAL FLOATING GATES, LOCAL SOURCE CONNECT	DE	2001-02-06				NXP B.V.
G 000212US	Granted	PROUD SILICIDE POLYSILICON TRENCH-GATE MOSFET	US	2001-07-24	2002-07-17	10/079651	US20030020102	NXP B.V.
G 000212US	Granted	PROUD SILICIDE POLYSILICON TRENCH-GATE MOSFET	US	2001-07-24	2002-07-17	10/733214	US20040124461	NXP B.V.
G 000212US	Granted	PROUD SILICIDE POLYSILICON TRENCH-GATE MOSFET	US	2001-07-24	2002-07-19	10/733214	US20060158801	NXP B.V.
G 000212US	Granted	PROUD SILICIDE POLYSILICON TRENCH-GATE MOSFET	US	2001-07-24	2002-08-06	10/713460	US20030047779	NXP B.V.
G 000212US	Granted	PROUD SILICIDE POLYSILICON TRENCH-GATE MOSFET	US	2001-09-13	2002-08-06	10/068920	US20020214116	NXP B.V.
G 000212US	Granted	MOSFET PRECISION CURRENT LIMIT/MEASURE SCHEME	FR	2001-02-22	2002-02-07	02/71159.0	FR1366569	NXP B.V.
G 000212US	Granted	MOSFET PRECISION CURRENT LIMIT/MEASURE SCHEME	DE	2001-02-22		02/71159.0	DE6040387	NXP B.V.
G 000212US	Granted	MOSFET PRECISION CURRENT LIMIT/MEASURE SCHEME	GB	2001-02-22		02/71159.0	GB1366569	NXP B.V.
G 000212US	Granted	EDGE TERMINATION BELOW CONNECTION FINGERS IN MOSFET	US	2001-09-04	2002-08-26	10/222672	US20030042456	NXP B.V.
G 000212US	Granted	FASCT MOSFET PLANNED TOS CARPING	US	2001-04-28	2002-04-26	10/34213	US2020166973	NXP B.V.
G 000212US	Granted	REDUCING LOSSES IN TRENCHMOS WITH INTRINSIC REGIONS	US	2002-09-20	2002-11-12	10/593991	US20030049650	NXP B.V.
G 000212US	Granted	COMPENSATED SENSEMOS	CN	2002-09-28		03/822899.8	CN1685119	NXP B.V.
G 000212US	Granted	COMPENSATED SENSEMOS	US	2002-09-28	2003-09-24	10/528941	US20060163652	NXP B.V.
G 000212US	Granted	TRENCHMOS WITH N/P HALO	US	2002-11-06	2003-10-12	10/533735	US20060043434	NXP B.V.
G 000212US	Granted	FEEDBACK SIGNAL FOR POWER SWITCHING CIRCUIT	US	2002-11-29	2003-11-19	10/536244	US20060066288	NXP B.V.
G 000212US	Granted	FEEDBACK SIGNAL FOR POWER SWITCHING CIRCUIT	DE	2002-11-29		03/812242.8	DE60342503	NXP B.V.
G 000212US	Granted	TRENCHMOS WITH TRENCHED FIELD PLATE BELOW GATE	US	2002-05-31	2003-05-21	10/515748	US20050173758	NXP B.V.
G 000212US	Granted	TRENCHMOS WITH TRENCHED FIELD PLATE BELOW GATE	FR	2002-05-31		03/73542.9	FR1535621	NXP B.V.
G 000212US	Granted	TRENCHMOS WITH TRENCHED FIELD PLATE BELOW GATE	DE	2002-05-31		03/73542.9	DE60358736	NXP B.V.
G 000212US	Granted	TRENCHMOS WITH TRENCHED FIELD PLATE BELOW GATE	GB	2002-05-31		03/73542.9	GB1525621	NXP B.V.
G 000212US	Granted	TRENCHMOS WITH TRENCHED FIELD PLATE BELOW GATE	US	2002-10-04	2003-09-15	10/529731	US20060010884	NXP B.V.
G 000212US	Granted	TRENCHMOS - DMOS HYBRID	US	2002-10-04	2004-05-21	10/561531	US20102911815	NXP B.V.
G 000212US	Granted	EDGE TERMINATION USING LATERAL MOSFETS	CN	2003-06-20		2004/80017151.2	CN1609931	NXP B.V.
G 000212US	Granted	BI-DIRECTIONAL TRENCHMOS	US	2003-06-20	2004-06-10	10/562254	US20060202305	NXP B.V.
G 000212US	Granted	BI-DIRECTIONAL TRENCHMOS WITH SURFACE FIELD REDUCING STRUCT	US	2003-06-20	2004-06-10	10/562254	US20060202305	NXP B.V.
G 000212US	Granted	SUBCHANNEL REGION WITH FIELD PLATE	US	2003-11-29	2004-11-26	10/561732	US20080203473	NXP B.V.
G 000212US	Granted	DEEP TRENCH DIELECTRIC WITH GRADED DOPING	CN	2003-11-29		2004/80035232.6	CN1868686	NXP B.V.
G 000212US	Granted	DEEP TRENCH DIELECTRIC WITH GRADED DOPING	US	2003-11-29	2004-11-26	10/580619	US20070124014	NXP B.V.
G 000212US	Granted	Trench Field Effect Transistor and Method of Making It	US	2004-03-03	2004-11-26	10/580619	US20070124014	NXP B.V.
G 000212US	Granted	FSI TRENCHMOS PROCESS	CN	2004-03-03	2005-02-23	10/591192	US20070181940	NXP B.V.
G 000212US	Granted	FSI TRENCHMOS PROCESS	US	2004-03-10	2005-02-28	2005/80007471.4	CN1930689	NXP B.V.
G 000212US	Granted	FSI TRENCHMOS PROCESS	CN	2004-03-10	2005-02-28	10/591352	US20070181975	NXP B.V.
G 000212US	Granted	Trench-Gate Transistors and their Manufacture	US	2004-03-10	2005-02-28	12/7041117	US20080150021	NXP B.V.
G 000212US	Granted	RESURF MOSFET WITH SI CARBIDE LAYER	CN	2004-03-31		2005/80010342.0	CN1947261	NXP B.V.
G 000212US	Granted	RESURF MOSFET WITH SI CARBIDE LAYER	US	2004-03-31	2005-03-29	10/594887	US20070222019	NXP B.V.
G 000212US	Granted	RESURF MOSFET WITH SI CARBIDE LAYER	JP	2004-03-31		2007-505726	JP4932701	NXP B.V.
G 000212US	Granted	POWERMOS WITH CELLS OF DIFFERENT THRESHOLD VOLTAGE	US	2004-07-20	2005-07-18	11/688223	US20080315278	NXP B.V.
G 000212US	Granted	DIVIDED GATE DRIVE FOR HIGH GAIN MOSFETS	US	2004-07-20	2005-07-18	11/688224	US20090212946	NXP B.V.
G 000212US	Granted	A LOW VOLTAGE TUNABLE TRENCH MOSFET	US	2004-09-08	2005-09-06	11/574973	US20080064166	NXP B.V.
G 000212US	Granted	3 TERMINAL MOSFET WITH TEMPERATURE SENSE FACILITY	CN	2005-03-15	2006-03-14	2005/80003839.X	CN20050008339	NXP B.V.
G 000212US	Granted	3 TERMINAL MOSFET WITH TEMPERATURE SENSE FACILITY	US	2005-03-24	2006-03-14	11/690664	US20090066404	NXP B.V.
G 000212US	Granted	BURIED LAYERS IN A SILICON PROCESS	US	2005-03-24	2006-03-14	10/7909446	US20070227764	NXP B.V.
N 015592US	Granted	SPAD DIODE PACKAGE WITH CONDUCTIVE STRIPS	US	1995-05-12	1996-05-13	08/645436	US5772100	NXP B.V.
N 015595US	Granted	SPAD PACKAGE FOR GSP DIODE WITH CONTACT PIN	US	1995-12-14	1996-12-10	08/762515	US5752197	NXP B.V.
N 016143US	Granted	HY-ADMOST WITH INACTIVE FINGER TIPS	US	1996-12-23	1997-12-22	08/959467	US5910670	NXP B.V.
N 016298US	Granted	MAKING A DEVICE WITH SHALLOW TRENCH ISOLATION	US	1997-04-07	1998-03-19	09/044644	US5966616	NXP B.V.
N 016509US	Granted	FABRICATION METHOD FOR SCHOTTKY DIODES	US	1997-09-03	1998-08-27	09/141644	US6218822	NXP B.V.
N 017214US	Granted	TRENCHMOST USING RESURF	US	1998-11-28	1999-11-29	09/450229	US6544817	NXP B.V.

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N1017521US	Granted	TRENCH MOST EDGE TERMINATION BY WIDE/DEEP TRENCH	US	1999-07-22	2000-07-24	09/624481		US6359308	NXP B.V.
N1017666US	Granted	SELF-ALIGNED TRENCH FET PROCESS USING SOURCE DIFFUSION	US	1999-09-28	2000-09-28	09/671888		US6368921	NXP B.V.
N1017731US	Granted	CSP FOR POWER TRANSISTORS	US	1999-11-11	2000-11-10	09/709663		US6442075	NXP B.V.
N1017960US	Granted	SELF-ALIGNED TRENCH MOST PROCESS WITH SIDE-WALL SOURCE	US	1999-11-30	2000-11-29	09/725410		US6459807	NXP B.V.
N1000065US	Granted	MULTI-RESURF DIODE WITH SEMI-INSULATING LAYERS	US	2000-02-12	2001-02-12	08/781498		US6436779	NXP B.V.
N1000131US	Granted	LV-MOSFET WITH I OF N DRAIN CONNECTION PLUG	US	2000-03-10	2001-03-09	09/603235		US6660194	NXP B.V.
N1000162US	Granted	LATERAL DEEP-TRENCH RESURF MOS DEVICE	FR	2000-03-23		019153295		FR1208860	NXP B.V.
N1000162DE	Granted	LATERAL DEEP-TRENCH RESURF MOS DEVICE	DE	2000-03-23		019153295		DE60132158	NXP B.V.
N1000162GB	Granted	LATERAL DEEP-TRENCH RESURF MOS DEVICE	GB	2000-03-23		019153295		GB1208600	NXP B.V.
N1000247FR	Granted	STEPPED OXIDE FABRICATION IN INVERSE-TRENCH MOS	FR	2000-04-26	2001-04-24	09/840816		US6319777	NXP B.V.
N1000247DE	Granted	STEPPED OXIDE FABRICATION IN INVERSE-TRENCH MOS	DE	2000-04-26		019366228.4		FR1281200	NXP B.V.
N1000247US	Granted	STEPPED OXIDE FABRICATION IN INVERSE-TRENCH MOS	US	2000-04-26	2001-05-18	09/866311		US6559502	NXP B.V.
N1000299US	Granted	LATERAL TRENCH MOS GATE COOL-MOS EXTENSIONS	US	2000-05-20		019439310.1		US6129542	NXP B.V.
N100029962	Granted	LATERAL TRENCH MOS GATE COOL-MOS EXTENSIONS	GB	2000-05-20		019439310.1		GB1295442	NXP B.V.
N1000299D1	Granted	LATERAL TRENCH MOS GATE COOL-MOS EXTENSIONS	DE	2000-05-20		019439310.1		DE60121331	NXP B.V.
N1000299R1	Granted	LATERAL TRENCH MOS GATE COOL-MOS EXTENSIONS	FR	2000-05-20		019439310.1		FR1289542	NXP B.V.
N1010060US	Granted	SELF-ALIGNED TRENCH MOS FABRICATION	US	2001-01-23	2002-06-04	10/055350		US6521498	NXP B.V.
N1010060DE09	Granted	SELF-ALIGNED TRENCH MOS FABRICATION	DE	2001-01-23		02734870.5		DE60232855	NXP B.V.
N1010060US	Granted	EDGE TERMINATIONS FOR RESURF-TRENCH-GATE MOSFETS	US	2001-09-13	2002-09-10	10/236175		US6926890	NXP B.V.
N1010664US	Granted	EDGE TERMINATIONS FOR RESURF-TRENCH-GATE MOSFETS	US	2001-09-13	2002-09-10	10/236795		US6833583	NXP B.V.
N1010926US	Granted	Combination of a Control Unit and a Logic Application, in which the Combination is Connected to a System	US	2001-12-18	2002-12-12	10/317386		US6841875	NXP B.V.
N1020933CN	Granted	MOSFET WITH TWO-STEPPED BOTTOM FRAME	CN	2002-10-07	2003-09-18	03823866.7		CN1689157	NXP B.V.
N1020933US	Granted	MOSFET WITH TWO-STEPPED BOTTOM FRAME	US	2002-10-07	2003-09-19	10/530304		US720700630.1	NXP B.V.
N1021021US	Granted	FALSESAFE METHOD AND CIRCUIT	US	2002-10-21	2003-09-19	10/531398		US7265574	NXP B.V.
N1021358US1	Granted	INTEGRATED HALF-BRIDGE POWER CIRCUIT	US	2002-12-10	2003-12-08	10/537575		US749750	NXP B.V.
N1021416US	Granted	TRENCH MOSFET WITH SIDEWALL GATE	US	2002-12-14	2003-12-08	10/538216		US7262460	NXP B.V.
N1021416FR08	Granted	TRENCH MOSFET WITH SIDEWALL GATE	FR	2002-12-14		03813280.9		FR1573824	NXP B.V.
N1021416DE09	Granted	TRENCH MOSFET WITH SIDEWALL GATE	DE	2002-12-14		03813280.9		DE60130451	NXP B.V.
N1021416GB10	Granted	TRENCH MOSFET WITH SIDEWALL GATE	GB	2002-12-14		03813280.9		GB1573824	NXP B.V.
N1021418US	Granted	THICK TRENCH BOTTOM OXIDE BY OXIDATION OF POLY-SI	US	2002-12-14	2003-12-08	10/538212		US7199010	NXP B.V.
N1030179US1	Granted	PUNCH-THROUGH DIODES, CONTROLLING THE CLAMPING	US	2003-02-18	2004-02-12	10/545622		US7482669	NXP B.V.
N1030179US2	Granted	PUNCH-THROUGH DIODES, CONTROLLING THE CLAMPING	US	2003-02-18	2004-02-12	12/239267		US7728404	NXP B.V.
N1031245CN1	Granted	SWITCH	CN	2003-10-23	2004-10-13	200480031154.1		CN200480031154	NXP B.V.
N1031245US1	Granted	SWITCH	US	2003-10-23	2004-10-13	10/577085		US7304526	NXP B.V.
N1031245FR02	Granted	SWITCH	FR	2003-10-23		06470248.5		FR1678828	NXP B.V.
N1031245DE03	Granted	SWITCH	DE	2003-10-23		06470248.5		DE602004037647	NXP B.V.
N1031245GB04	Granted	SWITCH	GB	2003-10-23		06470248.5		GB1678828	NXP B.V.
N1040812CN1	Granted	STACKED DIE PACKAGE (IC ON ESD DEVICE)	CN	2004-07-13	2005-07-06	200580023520.3		CN1585370	NXP B.V.
N1040812US1	Granted	SHALLOW TRENCH ISOLATION METHOD FOR FORMING	US	2004-07-13	2000-03-06	09/519310		US7090001607	NXP B.V.
N1040812US2	Granted	TRENCH DIFFUSION CORNER ROUNDING IN A	US	2004-07-13	2000-03-07	09/519308		US6346283	NXP B.V.
N1040812US3	Granted	VOLTAGE STABILIZED LOW LEVEL DRIVER	US	2004-07-13	2000-08-17	09/642181		US6433622	NXP B.V.
N1040812US4	Granted	VOLTAGE STABILIZED LOW LEVEL DRIVER	US	2004-07-13	2000-08-17	01958069.5		FR1312166	NXP B.V.
N1040812US5	Granted	VOLTAGE STABILIZED LOW LEVEL DRIVER	US	2004-07-13	2000-08-17	01958069.5		DE6013892	NXP B.V.
N1040812US6	Granted	VOLTAGE STABILIZED LOW LEVEL DRIVER	US	2004-07-13	2000-08-17	01958069.5		US6222353	NXP B.V.
N1040812US7	Granted	VOLTAGE STABILIZED LOW LEVEL DRIVER	US	2004-07-13	2000-08-17	01958069.5		US6222353	NXP B.V.
N1040812US8	Granted	VOLTAGE STABILIZED LOW LEVEL DRIVER	US	2004-07-13	2000-08-17	01958069.5		US6222353	NXP B.V.
N1040812US9	Granted	VOLTAGE STABILIZED LOW LEVEL DRIVER	US	2004-07-13	2000-08-17	01958069.5		US6222353	NXP B.V.
N1040812US10	Granted	VOLTAGE STABILIZED LOW LEVEL DRIVER	US	2004-07-13	2000-08-17	01958069.5		US6222353	NXP B.V.
N1040812US11	Granted	VOLTAGE STABILIZED LOW LEVEL DRIVER	US	2004-07-13	2000-08-17	01958069.5		US6222353	NXP B.V.
N1040812US12	Granted	VOLTAGE STABILIZED LOW LEVEL DRIVER	US	2004-07-13	2000-08-17	01958069.5		US6222353	NXP B.V.
N1040812US13	Granted	VOLTAGE STABILIZED LOW LEVEL DRIVER	US	2004-07-13	2000-08-17	01958069.5		US6222353	NXP B.V.
N1040812US14	Granted	VOLTAGE STABILIZED LOW LEVEL DRIVER	US	2004-07-13	2000-08-17	01958069.5		US6222353	NXP B.V.
N1040812US15	Granted	VOLTAGE STABILIZED LOW LEVEL DRIVER	US	2004-07-13	2000-08-17	01958069.5		US6222353	NXP B.V.
N1040812US16	Granted	VOLTAGE STABILIZED LOW LEVEL DRIVER	US	2004-07-13	2000-08-17	01958069.5		US6222353	NXP B.V.
N1040812US17	Granted	VOLTAGE STABILIZED LOW LEVEL DRIVER	US	2004-07-13	2000-08-17	01958069.5		US6222353	NXP B.V.
N1040812US18	Granted	VOLTAGE STABILIZED LOW LEVEL DRIVER	US	2004-07-13	2000-08-17	01958069.5		US6222353	NXP B.V.
N1040812US19	Granted	VOLTAGE STABILIZED LOW LEVEL DRIVER	US	2004-07-13	2000-08-17	01958069.5		US6222353	NXP B.V.
N1040812US20	Granted	VOLTAGE STABILIZED LOW LEVEL DRIVER	US	2004-07-13	2000-08-17	01958069.5		US6222353	NXP B.V.
N1040812US21	Granted	VOLTAGE STABILIZED LOW LEVEL DRIVER	US	2004-07-13	2000-08-17	01958069.5		US6222353	NXP B.V.
N1040812US22	Granted	VOLTAGE STABILIZED LOW LEVEL DRIVER	US	2004-07-13	2000-08-17	01958069.5		US6222353	NXP B.V.
N1040812US23	Granted	VOLTAGE STABILIZED LOW LEVEL DRIVER	US	2004-07-13	2000-08-17	01958069.5		US6222353	NXP B.V.
N1040812US24	Granted	VOLTAGE STABILIZED LOW LEVEL DRIVER	US	2004-07-13	2000-08-17	01958069.5		US6222353	NXP B.V.
N1040812US25	Granted	VOLTAGE STABILIZED LOW LEVEL DRIVER	US	2004-07-13	2000-08-17	01958069.5		US6222353	NXP B.V.
N1040812US26	Granted	VOLTAGE STABILIZED LOW LEVEL DRIVER	US	2004-07-13	2000-08-17	01958069.5		US6222353	NXP B.V.
N1040812US27	Granted	VOLTAGE STABILIZED LOW LEVEL DRIVER	US	2004-07-13	2000-08-17	01958069.5		US6222353	NXP B.V.
N1040812US28	Granted	VOLTAGE STABILIZED LOW LEVEL DRIVER	US	2004-07-13	2000-08-17	01958069.5		US6222353	NXP B.V.
N1040812US29	Granted	VOLTAGE STABILIZED LOW LEVEL DRIVER	US	2004-07-13	2000-08-17	01958069.5		US6222353	NXP B.V.
N1040812US30	Granted	VOLTAGE STABILIZED LOW LEVEL DRIVER	US	2004-07-13	2000-08-17	01958069.5		US6222353	NXP B.V.
N1040812US31	Granted	VOLTAGE STABILIZED LOW LEVEL DRIVER	US	2004-07-13	2000-08-17	01958069.5		US6222353	NXP B.V.
N1040812US32	Granted	VOLTAGE STABILIZED LOW LEVEL DRIVER	US	2004-07-13	2000-08-17	01958069.5		US6222353	NXP B.V.
N1040812US33	Granted	VOLTAGE STABILIZED LOW LEVEL DRIVER	US	2004-07-13	2000-08-17	01958069.5		US6222353	NXP B.V.
N1040812US34	Granted	VOLTAGE STABILIZED LOW LEVEL DRIVER	US	2004-07-13	2000-08-17	01958069.5		US6222353	NXP B.V.
N1040812US35	Granted	VOLTAGE STABILIZED LOW LEVEL DRIVER	US	2004-07-13	2000-08-17	01958069.5		US6222353	NXP B.V.
N1040812US36	Granted	VOLTAGE STABILIZED LOW LEVEL DRIVER	US	2004-07-13	2000-08-17	01958069.5		US6222353	NXP B.V.
N1040812US37	Granted	VOLTAGE STABILIZED LOW LEVEL DRIVER	US	2004-07-13	2000-08-17	01958069.5		US6222353	NXP B.V.
N1040812US38	Granted	VOLTAGE STABILIZED LOW LEVEL DRIVER	US	2004-07-13	2000-08-17	01958069.5		US6222353	NXP B.V.
N1040812US39	Granted	VOLTAGE STABILIZED LOW LEVEL DRIVER	US	2004-07-13	2000-08-17	01958069.5		US6222353	NXP B.V.
N1040812US40	Granted	VOLTAGE STABILIZED LOW LEVEL DRIVER	US	2004-07-13	2000-08-17	01958069.5		US6222353	NXP B.V.
N1040812US41	Granted	VOLTAGE STABILIZED LOW LEVEL DRIVER	US	2004-07-13	2000-08-17	01958069.5		US6222353	NXP B.V.
N1040812US42	Granted	VOLTAGE STABILIZED LOW LEVEL DRIVER	US	2004-07-13	2000-08-17	01958069.5		US6222353	NXP B.V.
N1040812US43	Granted	VOLTAGE STABILIZED LOW LEVEL DRIVER	US	2004-07-13	2000-08-17	01958069.5		US6222353	NXP B.V.
N1040812US44	Granted	VOLTAGE STABILIZED LOW LEVEL DRIVER	US	2004-07-13	2000-08-17	01958069.5		US6222353	NXP B.V.
N1040812US45	Granted	VOLTAGE STABILIZED LOW LEVEL DRIVER	US	2004-07-13	2000-08-17	01958069.5		US6222353	NXP B.V.
N1040812US46	Granted	VOLTAGE STABILIZED LOW LEVEL DRIVER	US	2004-07-13	2000-08-17	01958069.5		US6222353	NXP B.V.
N1040812US47	Granted	VOLTAGE STABILIZED LOW LEVEL DRIVER	US	2004-07-13	2000-08-17	01958069.5		US6222353	NXP B.V.
N1040812US48	Granted	VOLTAGE STABILIZED LOW LEVEL DRIVER	US	2004-07-13	2000-08-17	01958069.5		US6222353	NXP B.V.
N1040812US49	Granted	VOLTAGE STABILIZED LOW LEVEL DRIVER	US	2004-07-13	2000-08-17	01958069.5		US6222353	NXP B.V.
N1040812US50	Granted	VOLTAGE STABILIZED LOW LEVEL DRIVER	US	2004-07-13	2000-08-17	01958069.5		US6222353	NXP B.V.
N1040812US51	Granted	VOLTAGE STABILIZED LOW LEVEL DRIVER	US	2004-07-13	2000-08-17	01958069.5		US6222353	NXP B.V.
N1040812US52	Granted	VOLTAGE STABILIZED LOW LEVEL DRIVER	US	2004-07-13	2000-08-17	01958069.5		US6222353	NXP B.V.
N1040812US53	Granted	VOLTAGE STABILIZED LOW LEVEL DRIVER	US	2004-07-13	2000-08-17	01958069.5		US6222353	NXP B.V.
N1040812US54	Granted	VOLTAGE STABILIZED LOW LEVEL DRIVER	US	2004-07-13	2000-08-17	01958069.5		US6222353	NXP B.V.
N1040812US55	Granted	VOLTAGE STABILIZED LOW LEVEL DRIVER	US	2004-07-13	2000-08-17	01958069.5		US6222353	NXP B.V.
N1040812US56	Granted	VOLTAGE STABILIZED LOW LEVEL DRIVER	US	2004-07-13	2000-08-17	01958069.5		US6222353	NXP B.V.
N1040812US57	Granted	VOLTAGE STABILIZED LOW LEVEL DRIVER	US	2004-07-13	2000-08-17	01958069.5		US6222353	NXP B.V.
N1040812US58	Granted	VOLTAGE STABILIZED LOW LEVEL DRIVER	US	2004-07-13	2000-08-17	01958069.5		US6222353	NXP B.V.
N1040812US59	Granted	VOLTAGE STABILIZED LOW LEVEL DRIVER	US	2004-07-13	2000-08-17	01958069.5		US6222353	NXP B.V.
N1040812US60	Granted	VOLTAGE STABILIZED LOW LEVEL DRIVER	US						